

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2021 to Q4/2021

Based on structural similarity

	User Part Number BC51-10PAS					
boratory	Part Description					
	Nexperia DHAM Small Signal Bipolar Transistor					
iability labs	MCD package					
EC-Q101 Test	Test Conditions	Duration	# Lots	# Quantity	# Rejects	
TEST						
Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below	
	JESD22-A113					
					_	
Preconditioning		3 cycles	208	16640	0	
					_	
DIdS	reverse voltage	1000 hours	202	16160	0	
T-0	JECD22 A104					
		1000	F2	4160	0	
remperature cycling	• '	1000 cycles	52	4160	0	
46						
		OC have	F2	4160	0	
Autociave	Fressure = 203 KFa (23.7 psia)	96 nours	52	4160	U	
HOTER	JESD22-Δ101					
		1000 hours	E2	4160	0	
remperature neverse bias		1000 110015	32	4100	U	
TOL						
		1000 hours	E2	4160	0	
incommetent Operating Life	100 6 101 13000 676163	1000 Hours	32	4100	U	
DSH	JESD22-Δ111					
		10 c	n a	n a	n.a.	
		10.5	11.a.	11.a.	11.0.	
Solderability	J-STD-002		111	1110	0	
i	PC Preconditioning  HTRB High Temperature Reverse Bias  TC Temperature Cycling  AC Autoclave  H3TRB High Humidity High Temperature Reverse Bias  IOL Intermittent Operating Life  RSH Resistance to Solder Heat SD	BCS1-10PAS  boratory  Part Description Nexperia DHAM MCD package  EC-Q101 Test Test Conditions  TEST Pre- and Post-Stress Electrical Test  Tamb = 25 °C  JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Preconditioning  MIL-STD-750-1 M1039 Method A Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage  TC Temperature Cycling  AC Autoclave  H3TRB High Humidity High Temperature Reverse Bias  JESD22-A102 Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)  JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of rated reverse voltage  MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔTj = 100 °C for 15000 cycles  RSH Resistance to Solder Heat  JESD22-A111 Z60 °C ± 5 °C	BC51-10PAS	BC51-10PAS	BC51-10PAS   BC51-10PAS   Brank   B	

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

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